

ARTICLE

Received 8 Aug 2016 | Accepted 20 Mar 2017 | Published 8 May 2017

DOI: 10.1038/ncomms15306

OPEN

# Highly selective covalent organic functionalization of epitaxial graphene

Rebeca A. Bueno<sup>1</sup>, José I. Martínez<sup>1</sup>, Roberto F. Luccas<sup>1,2</sup>, Nerea Ruiz del Árbol<sup>1</sup>, Carmen Munuera<sup>1</sup>, Irene Palacio<sup>1</sup>, Francisco J. Palomares<sup>1</sup>, Koen Lauwaet<sup>1</sup>, Sangeeta Thakur<sup>3</sup>, Jacek M. Baranowski<sup>4</sup>, Wlodek Strupinski<sup>4</sup>, María F. López<sup>1</sup>, Federico Mompean<sup>1</sup>, Mar García-Hernández<sup>1</sup> & José A. Martín-Gago<sup>1</sup>

Graphene functionalization with organics is expected to be an important step for the development of graphene-based materials with tailored electronic properties. However, its high chemical inertness makes difficult a controlled and selective covalent functionalization, and most of the works performed up to the date report electrostatic molecular adsorption or unruly functionalization. We show hereafter a mechanism for promoting highly specific covalent bonding of any amino-terminated molecule and a description of the operating processes. We show, by different experimental techniques and theoretical methods, that the excess of charge at carbon dangling-bonds formed on single-atomic vacancies at the graphene surface induces enhanced reactivity towards a selective oxidation of the amino group and subsequent integration of the nitrogen within the graphene network. Remarkably, functionalized surfaces retain the electronic properties of pristine graphene. This study opens the door for development of graphene-based interfaces, as nano-bio-hybrid composites, fabrication of dielectrics, plasmonics or spintronics.

<sup>1</sup>Materials Science Factory, Instituto de Ciencia de Materiales de Madrid-CSIC, C/Sor Juana Inés de la Cruz 3, Madrid 28049, Spain. <sup>2</sup>Instituto de Física Rosario-CONICET-UNR, Bv. 27 de Febrero 210bis, Rosario S2000EZF, Argentina. <sup>3</sup>Sincrotrone Trieste, strada Statale 14 - km 163, Basovizza 5 34149, Italy. <sup>4</sup>Institute of Electronic Materials Technology, Wolczynska 133, 01-919 Warsaw, Poland. Correspondence and requests for materials should be addressed to J.A.M.-G. (email: gago@icmm.csic.es).